October 1993 Revised January 1999

74ABT16543 16-Bit Registered Transceiver with 3-STATE Outputs

General Description

FAIRCHILD

SEMICONDUCTOR

The ABT16543 16-bit transceiver contains two sets of Dtype latches for temporary storage of data flowing in either direction. Separate Latch Enable and Output Enable inputs are provided for each register to permit independent control of inputting and outputting in either direction of data flow. Each byte has separate control inputs, which can be shorted together for full 16-bit operation.

Features

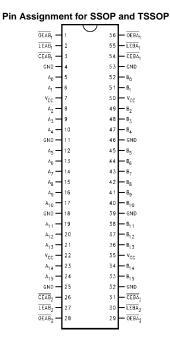
- Back-to-back registers for storage
- Bidirectional data path
- A and B outputs have current sourcing capability of 32 mA and current sinking capability of 64 mA
- Separate control logic for each byte
- 16-bit version of the ABT543
- Separate controls for data flow in each direction
- Guaranteed latchup protection
- High impedance glitch free bus loading during entire power up and power down cycle
- Nondestructive hot insertion capability

Ordering Code:

	Order Number	Package Number	Package Description			
	74ABT16543CSSC	MS56A	56-Lead Shrink Small Outline Package (SSOP), JEDEC MO-118, 0.300" Wide			
	74ABT16543CMTD MTD56		56-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide			
Devices also available on Tana and Real. Specify by appending the suffix latter "V" to the ordering code						

Devices also available on Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

Connection Diagram

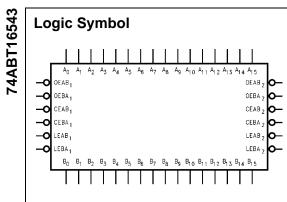


Pin Descriptions

Pin Names	Description
OEAB	A-to-B Output Enable Input (Active LOW)
OEBAn	B-to-A Output Enable Input (Active LOW)
CEAB	A-to-B Enable Input (Active LOW)
CEBAn	B-to-A Enable Input (Active LOW)
LEAB _n	A-to-B Latch Enable Input (Active LOW)
LEBAn	B-to-A Latch Enable Input (Active LOW)
A ₀ -A ₁₅	A-to-B Data Inputs or
	B-to-A 3-STATE Outputs
B ₀ -B ₁₅	B-to-A Data Inputs or
	A-to-B 3-STATE Outputs

74ABT16543 16-Bit Registered Transceiver with 3-STATE Outputs

© 1999 Fairchild Semiconductor Corporation DS011646.prf



Data I/O Control Table

	Inputs		Latch Status	Output Buffers	
CEAB _n	LEAB _n	OEAB _n	(Byte n)	(Byte n)	
Н	Х	Х	Latched	HIGH Z	
Х	н	Х	Latched	—	
L	L	Х	Transparent	_	
х	Х	н	_	HIGH Z	
L	Х	L	—	Driving	

H = HIGH Voltage Level

L = LOW Voltage Level X = Immaterial

A-to-B data flow shown;

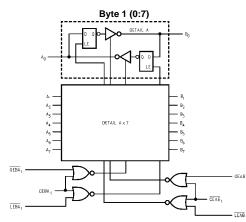
B-to-A flow control is the same, except using $\overline{\text{CEBA}}_n, \overline{\text{LEBA}}_n$ and $\overline{\text{OEBA}}_n$

Functional Description

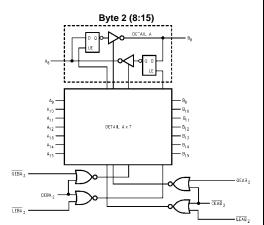
The ABT16543 contains two sets of D-type latches, with separate input and output controls for each. For data flow from A to B, for example, the A to B Enable (CEAB) input must be low in order to enter data from the A port or take data from the B-Port as indicated in the Data I/O Control Table. With CEAB low, a low signal on (LEAB) input makes the A to B latches transparent; a subsequent low to high transition of the LEAB line puts the A latches in the storage

mode and their outputs no longer change with the A inputs. With \overrightarrow{CEAB} and \overrightarrow{OEAB} both low, the B output buffers are active and reflect the data present on the output of the A latches. Control of data flow from B to A is similar, but using the \overrightarrow{CEBA} , \overrightarrow{LEBA} and \overrightarrow{OEBA} . Each byte has separate control inputs, allowing the device to be used as two 8-bit transceivers or as one 16-bit transceiver.

Logic Diagrams



Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.



Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings(Note 1)

		C
Storage Temperature	-65°C to +150°C	C
Ambient Temperature under Bias	-55°C to +125°C	R
Junction Temperature under Bias	-55°C to +150°C	C
V _{CC} Pin Potential to		Ŭ
Ground Pin	-0.5V to +7.0V	F
Input Voltage (Note 2)	-0.5V to +7.0V	5
Input Current (Note 2)	-30 mA to +5.0 mA	Ν
Voltage Applied to Any Output		
in the Disable or		
Power-Off State	-0.5V to +5.5V	
in the HIGH State	-0.5V to V _{CC}	No
Current Applied to Output		ma un
in LOW State (Max)	twice the rated I _{OL} (mA)	No

DC Latchup Source Current Over Voltage Latchup (I/O)

Recommended Operating Conditions

Free Air Ambient Temperature	$-40^{\circ}C$ to $+85^{\circ}C$
Supply Voltage	+4.5V to +5.5V
Minimum Input Edge Rate (ΔV/Δt)	
Data Input	50 mV/ns
Enable Input	20 mV/ns
Clock Input	100 mV/ns
Note 1: Absolute maximum ratings are value may be damaged or have its useful life imp under these conditions is not implied.	,

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

Symbol	Parameter	Min	Тур	Мах	Units	v _{cc}	Conditions
VIH	Input HIGH Voltage	2.0			V		Recognized HIGH Signal
V _{IL}	Input LOW Voltage			0.8	V		Recognized LOW Signal
V _{CD}	Input Clamp Diode Voltage			-1.2	V	Min	I _{IN} = -18 mA (Non I/O Pins)
V _{OH}	Output HIGH Voltage	2.5					$I_{OH} = -3 \text{ mA}, (A_n, B_n)$
		2.0					I _{OH} = -32 mA, (A _n , B _n)
V _{OL}	Output LOW Voltage			0.55	V	Min	$I_{OL} = 64 \text{ mA}, (A_n, B_n)$
V _{ID}	Input Leakage Test	4.75			V	0.0	I _{ID} = 1.9 μA, (Non-I/O Pins) All Other Pins Grounded
IIH	Input HIGH Current			1	μA	Max	V _{IN} = 2.7V (Non-I/O Pins) ((Note 3)
				1			$V_{IN} = V_{CC}$ (Non-I/O Pins)
I _{BVI}	Input HIGH Current Breakdown Test			7	μA	Max	$V_{IN} = 7.0V$ (Non-I/O Pins)
IBVIT	Input HIGH Current			100	μA	Max	$V_{IN} = 5.5V (A_n, B_n)$
	Breakdown Test (I/O)						
IIL	Input LOW Current			-1	μA	Max	V _{IN} = 0.5V (Non-I/O Pins) (Note 3)
				-1			V _{IN} = 0.0V (Non-I/O Pins)
I _{IH} + I _{OZH}	Output Leakage Current			10	μA	0V-5.5V	$V_{OUT} = 2.7V (A_n, B_n);$
							\overline{OEAB} or $\overline{CEAB} = 2V$
I _{IL} + I _{OZL}	Output Leakage Current			-10	μA	0V-5.5V	$V_{OUT} = 0.5V (A_n, B_n);$
							\overline{OEAB} or $\overline{CEAB} = 2V$
I _{OS}	Output Short-Circuit Current	-100		-275	mA	Max	$V_{OUT} = 0V (A_n, B_n)$
I _{CEX}	Output HIGH Leakage Current			50	μA	Max	$V_{OUT} = V_{CC} (A_n, B_n)$
I _{ZZ}	Bus Drainage Test			100	μA	0.0V	V _{OUT} = 5.5V (A _n , B _n); All Others GND
I _{CCH}	Power Supply Current			1.0	mA	Max	All Outputs HIGH
I _{CCL}	Power Supply Current			60	mA	Max	All Outputs LOW
I _{CCZ}	Power Supply Current			1.0	mA	Max	Outputs 3-STATE
							All Others at V_{CC} or GND
I _{CCT}	Additional I _{CC} /Input			2.5	mA	Max	$V_I = V_{CC} - 2.1V$
	<u> </u>						All Others at V_{CC} or GND
I _{CCD}	Dynamic I _{CC} No Load						Outputs Open, \overline{CEAB} , \overline{OEAB} , $\overline{LEAB} = GND$
	(Note 3)			0.25	mA/MHz	Max	$\overline{CEBA} = V_{CC}$, One Bit Toggling,
							50% Duty Cycle

74ABT16543

–500 mA 10V

74ABT16543

AC Electrical Characteristics

Symbol	Parameter		$T_{A} = +25^{\circ}C$ $V_{CC} = +5.0V$ $C_{L} = 50 \text{ pF}$			$T_A = -55^{\circ}C \text{ to } +85^{\circ}C$ $V_{CC} = 4.5V - 5.5V$ $C_L = 50 \text{ pF}$	
		Min	Тур	Max	Min	Max	
t _{PLH}	Propagation Delay	1.5	3.0	5.7	1.5	5.7	ns
t _{PHL}	A _n to B _n or B _n to A _n						
t _{PLH}	Propagation Delay	1.5	3.0	5.5	1.5	5.5	ns
t _{PHL}	$\overline{\text{LEAB}}_{\overline{n}}$ to B _n , $\overline{\text{LEBA}}_{\overline{n}}$ to A _n						
t _{PZH}	Enable Time	1.5	2.8	5.2	1.5	5.2	ns
t _{PZL}	$\overline{OEBA_n}$ or $\overline{OEAB_n}$ to A_n or B_n						
t _{PHZ}	Disable Time	1.6	3.1	6.0	1.6	6.0	ns
t _{PLZ}	\overline{OEAB}_n or \overline{OEBA}_n to A_n or B_n						
t _{PZH}	Enable Time	1.5	3.1	6.2	1.5	6.2	ns
t _{PZL}	$\overline{\text{CEBA}}_n$ or $\overline{\text{CEAB}}_n$ to A_n or B_n						
t _{PHZ}	Disable Time	1.7	3.2	6.3	1.7	6.3	ns
t _{PLZ}	\overline{CEBA}_n or \overline{CEAB}_n to A_n or B_n						

AC Operating Requirements

(SSOP Package)

Symbol	Parameter	$T_A = +25^{\circ}C$ $V_{CC} = +5.0V$ $C_L = 50 \text{ pF}$		$T_A = -55^{\circ}C \text{ to } +85^{\circ}C$ $V_{CC} = 4.5V - 5.5V$ $C_L = 50 \text{ pF}$		Units
		Min	Max	Min	Max	
t _S (H)	Setup Time, HIGH or LOW	2.0		2.0		ns
t _S (L)	A_n or B_n to $\overline{LEBA_n}$ or $\overline{LEAB_n}$	2.0		2.0		
t _H (H)	Hold Time, HIGH or LOW	1.0		1.0		ns
t _H (L)	A_n or B_n to $\overline{LEBA_n}$ or $\overline{LEAB_n}$	1.0		1.0		
t _W (L)	Pulse Width, LOW	3.0		3.0		ns

Capacitance

Symbol	Parameter	Тур	Units	Conditions T _A = 25°C
C _{IN}	Input Capacitance	5.0	pF	V _{CC} = 0V (non I/O pins)
C _{I/O} (Note 4)	Output Capacitance	11.0	pF	$V_{CC} = 5.0V (A_n, B_n)$

Note 4: $C_{I/O}$ is measured at frequency, f = 1 MHz, per MIL-STD-883, Method 3012.

